









## **Table of Contents**

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• <b>High Reliability Screening</b>







 Sales Representatives / Contact. back cover



### SSDI is JANS certified / ISO 9001 and AS9100 certified

SSDI is a world-renowned leader in the design and manufacture of semiconductors, assemblies, and modules. As a pioneer semiconductor manufacturer for over 50 years, SSDI has earned and maintained a reputation for setting the highest standards of reliability and performance. This reputation has been built upon unsurpassed technology and quality in the areas of high density / high power and high voltage discrete semiconductors and modules.

SSDI operates three facilities within a 3-mile area in the city of La Mirada, California



Firestone Facility



**Knott Facility** 



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#### **Warnings**

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact

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### SSDI LIFTS PROGRAMS TO NEW HEIGHTS BY FOCUSING ON:

## **HIGH RELIABILITY**

- 50+ years serving the HiRel market
- JANS certified and ISO 9001 / AS9100 certified
- 96% of sales for Aerospace and Defense applications

## PRODUCT INNOVATION

- Developing innovative, state of the art products: pushing the envelope with performance not matched by other manufacturers' products
- Exploring new technology (e.g. GaN, SiC, etc.)

## **SOLUTIONS**

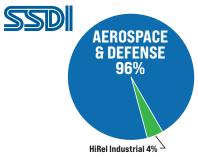
- Broad Capabilities: catalog showcases capability, not limited to current offerings
- Design Support / Flexibility: make adjustments to satisfy customer requirements
- Packaging Flexibility: improve density of board design which leads to overall system cost improvements
- Sustainment: support for the life of the program; work with customer to accommodate small to medium quantities

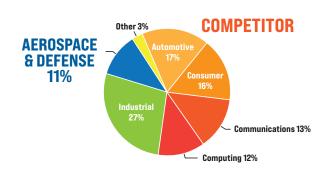




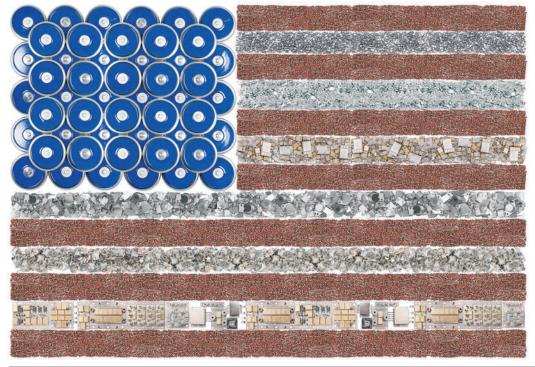


#### SALES BY SECTOR





### **WIDE RANGE OF HERMETIC PRODUCTS - MADE IN THE USA**



#### **SILICON**

- Rectifiers
- Schottkys
- PIN Diodes
- Zeners
- Thyristors

JFETs

- TVS
- IGBTs
- MOSFETs
- Bipolar Transistors

#### **SILICON CARBIDE (SiC)**

- MOSFETs

#### GALLIUM NITRIDE (GaN)

Power FETs

#### ASSEMBLY PRODUCTS

- LD0
- DC-DC Converters
- Hybrids
- Assemblies
- **Power Modules**

Notes: Minimum order may apply. Most products available in die form.

## SiC Schottkys & SiC MOSFETs Overview



## Silicon Carbide (SiC) Technology Advantages Beyond Si and GaAs:

SiC technology goes far beyond the performance of conventional silicon and GaAs rectifiers, offering significantly lower switching losses and higher switching frequencies, as well as higher operating voltages than GaAs rectifiers.

#### SiC increases performance in extreme conditions:

With SiC, you can meet the needs of your most demanding designs: tougher, smaller, more reliable designs able to withstand heat, radiation and survive under extreme environmental conditions.

#### SiC reduces complexity, system costs:

SiC allows applications to operate at high switching frequencies without complex resonant switching circuits or snubbers, which eliminates the need for large heat sinks and cooling fans. This decreases system costs and increases performance and reliability.

#### **Features**

- Electrical breakdown 10x Si and GaAs
- Operates up to 300°C without switching losses
- Thermal conductivity 3x Si and 10x GaAs
- Can easily be paralleled for higher currents (matching is not necessary with SiC products due to positive temperature coefficient and negligible reverse recovery time)

## **Featured SiC Schottkys**

## SSR12C50S.22 - SSR12C60S.22 12 A. 500 - 600 V SiC Schottkys

- No recovery time (t<sub>FR</sub> or t<sub>RR</sub>)
- No switching time change over temperature
- Low forward voltage drop
- Low reverse leakage current
- Hermetically sealed surface mount package
- Small footprint (0.157" W x 0.227" L x 0.075" H)

## SSR24C60CTJ Series 24 A, 300 - 600 V Center Tap SiC Schottkys

- Very high operating temperature: 250°C
- No recovery time (t<sub>FR</sub> or t<sub>RR</sub>)
- Hermetically sealed, isolated packaging
- High current operation
- Available in common cathode (CT) and common anode (CA) configurations



## SPA555 Series 32 A, 1000 - 1200 V SiC Schottky 1Φ Bridges

- No recovery time (t<sub>FR</sub> or t<sub>RR</sub>)
- No switching time change over temperature
- Small package size: (1.25" W x 1.25" L x 0.35" H, not including terminals)
- Cases with aluminum heat sink are available
- Terminal options: turret, copper leads, and surface mount



## Early proponent of hermetic SiC Schottkys

**Advantages of SSDI HiRel SiC Products** 

- Heritage including airborne / space flight applications
- High power / high voltage capabilities:
  - SiC Schottkys: up to 100 A, 2000 V
  - SiC MOSFETs: up to 200 A, 1700 V

#### Design flexibility:

- Target key electrical parameters to meet mission specific requirements
- Development of bridge assemblies / power modules

#### Hermetically sealed packaging / package flexibility:

- Wide variety of hermetic package options from high density, surface mount packages to legacy TO-25x and stud mount packages
- In-house machine shop / tooling capabilities provide package modifications to meet mission requirements

#### - High reliability screening:

- TX, TXV, and S level screening available
- Based on MIL-PRF-19500 (screening flows available on request)

## **Featured SiC MOSFETs**

### **SFC35N120 Series** 26 - 30 A, 1200 V, 30 ns typ SiC MOSFETs

- Fast switching, low capacitance
- Low  $R_{DS(ON)} = 80 \text{ m}\Omega \text{ typ}$
- Easy to parallel, simple to drive
- Enhancement mode N-channel

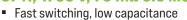


### **SFC85N90S1 / S2** 85 A, 900 V, 17 mΩ SiC MOSFETs

- Fast switching, low capacitance
- Low  $R_{DS(\Omega)} = 13 \text{ m}\Omega \text{ typ}$
- Easy to parallel, simple to drive
- Enhancement mode N-channel
- Hermetically sealed power packaging: SMD2 (S2), SMD1 (S1), SMD1 with leads (S1L)



# **SFC57N17OS1**57 A, 1700 V, 70 mΩ SiC MOSFETs



- Low  $R_{DS(\Omega N)} = 45 \text{ m}\Omega \text{ typ}$
- Easy to parallel, simple to drive
- Enhancement mode N-channel
- Hermetically sealed power packaging: SMD1 (S1), SMD1 with leads (S1L)



SMD1 with leads

(Customizable ribbon leads option reduces risk of vibration stress and thermal fatigue)

Consider SSDI's hermetic GaN Power FETs for aerospace and defense applications requiring faster switching capabilities:

- Hermetic, high voltage GaN solutions: 40 1000 V
- 8 W 50 W, 6.3 A 90 A

SPA555L

(copper leads)



## **SiC Schottkys**

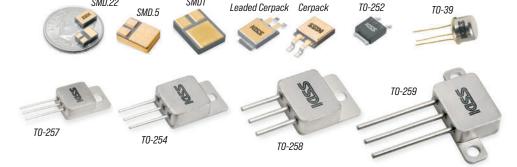
#### Sorted by $I_{\scriptscriptstyle 0}$ / $V_{\scriptscriptstyle R}$ - Ratings based on 25 $^{\circ}\text{C}$ case temperature

		1				1			
Part Number	I₀ [A]	V <sub>R</sub> [V]	I <sub>FSM</sub> [A]	V <sub>F</sub> typ [V]	V <sub>F</sub> max [V]	I <sub>R</sub> typ [μΑ]	I <sub>R</sub> max [μΑ]	Package	Data Sheet
SSR02C50 - SSR02C60	2	500 - 600	4	1.75	2	0.2	100	Cerpack, SMD.22	RS0204
SSR04C50CTG - SSR04C60CTG SSR04C50CTS.22 - SSR04C60CTS.22	4	500 - 600	8	1.8	2	0.2	100	Cerpack, SMD.22	SH0111
SSR04C50CT/39 - SSR04C60CT/39 SSR04C50CTS.5 - SSR04C60CTS.5	4	500 - 600	4	1.8	1.94	100	200	T0-39, SMD.5	RS0022
SSR05C50 - SSR05C60	5	500 - 600	40	1.4	1.8	0.1	10	Cerpack, SMD.22, SMD.5	SH0113
SSR05C100 - SSR05C120	5	1000 - 1200	30	1.65	1.8	2	100	Cerpack, Leaded Cerpack, SMD.5	SH0030
SSR10C20 - SSR10C30	10	200 - 300	18	1.5	1.65	25	100	Cerpack, SMD.5	RS0032
SSR10C30CTG - SSR10C60CTG	10	300 - 600	20	1.95	2	10	250	Cerpack	SH0036
SSR10C50S.22 - SSR10C60S.22	10	500 - 600	70	1.7	1.9	0.2	20	SMD.22	SH0131
SSR10C080J / M - SSR10C120J / M	10	800 - 1200	60	1.53	1.8	10	50	T0-257, T0-254	SH0080
SSR10C080 - SSR10C120	10	800 - 1200	50	1.5	2	10	100	Cerpack, Leaded Cerpack, SMD.5	SH0067
SSR12C50S.22 - SSR12C60S.22	12	500 - 600	50	1.54	1.75	3	25	SMD.22	SH0121
SSR25C50DM - SSR25C60DM	12.5	500 - 600	80	2	2.3	0.5	50	T0-254	RC0165
SSR15C50D1 - SSR15C120D1	15	500 - 1200	100	2.1	Note 1	1	200	T0-252	SH0114
SSR20C080CTS1 - SSR20C120CTS1	20	800 - 1200	50	2.1	2.5	40	500	SMD1	SH0049
SSR20C080CT - SSR20C120CT	20	800 - 1200	50	1.53	1.8	10	50	T0-257, T0-254	SH0029
SSR20C180	20	1800	Note 1	2	2.25	20	200	Cerpack, SMD.5	SH0128
SSR24C30CT - SSR24C60CT	24	300 - 600	50	1.5	1.7	1	200	Cerpack, SMD.5	RS0020
SSR24C30CAJ - SSR24C60CTJ	24	300 - 600	50	1.5	1.75	1	200	T0-257	RS0028
SSR25C50CAM - SSR25C60CTM	25	500 - 600	80	2	2.3	0.5	50	T0-254	RC0165
SPA555	32	1000 - 1200	125	1.45	1.53	20	100	SPA555	RA0038
SSR40C20CT - SSR40C60CT	40	200 - 600	150	1.65	1.75	1	50	Cerpack, SMD.5, TO-254	RS0024
SSR40C50D - SSR40C60D	40	500 - 600	100	2.03	2.2	10	250	T0-258, T0-259	SH0082
SSR40C100S1 - SSR40C120S1	40	1000 - 1200	200	1.45	1.65	30	100	SMD1	SH0043
SSR50C50CTM - SSR50C60CTM	50	500 - 600	100	1.6	1.9	20	250	T0-254	RC0140
SSR80C50CT - SSR80C60CA	80	500 - 600	100	2.03	2.2	10	250	T0-258, T0-259	SH0082

## For high reliability aerospace and defense applications such as:

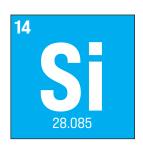
1/ Contact factory for more information

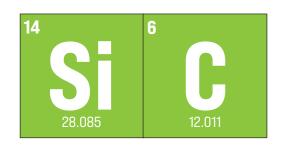
- High voltage power supplies
- Switches
- Power controls



## Si / SiC MOSFETs & GaN FETs









## **FAST**

Replacements available for most products from Infineon / IR, Texas Instruments, Vishay, etc.

## **FASTER**

Faster switching. rad tolerant replacements for Silicon MOSFETs

## **FASTEST**

Recommended for new designs requiring the fastest switching performance

### **Silicon MOSFETs**

- 10 A 250 A
- -200 V 1000 V
- 50 W 500 W
- Wide variety of package options and performance capabilities

### Silicon Carbide MOSFETs

- Up to 200 A
- Up to 1700 V
- Offers highest voltage capability compared to Silicon MOSFETs and **GaN FETs**
- Lower R<sub>DS(ON)</sub> than Silicon MOSFETs

### **Gallium Nitride FETs**

- 6.3 A 90 A
- 40 V 1000 V
- Lowest  $R_{nsronn}$ , ≥ 2.5 m $\Omega$
- Rad tolerant
- Highest voltage available for hermetic GaN FETs in the industry

## SiC MOSFETs

Sorted by V<sub>DSS</sub> / I<sub>D</sub> - Ratings based on 25°C case temperature

Part Number	V <sub>DSS</sub> [V]	I <sub>o</sub> [A]	$R_{DS(DN)}$ typ [m $\Omega$ ]	$R_{DS(ON)}$ max $[m\Omega]$	Q <sub>6</sub> typ [nC]	Q <sub>g</sub> max [nC]	P <sub>D</sub> [W]	Package	Data Sheet
SFC85N80S2	800	85	8.7	10	270	Note 1	326	SMD2	FT0105
SFC85N90S1	900	85	10	17	130	Note 1	288	SMD1	FT0083
SFC85N90S1L	900	85	10	17	130	Note 1	288	SMD1 with leads	FT0083
SFC85N90S2	900	85	10	17	130	Note 1	288	SMD2	FT0083
SFC200N90P6	900	200	7	10	420	Note 1	428	6 Pin T0-259 (P6)	FT0097
SFC35N120G	1200	26	80	96	46	65	64	Cerpack	FT0079
SFC35N120S.5	1200	26	80	96	46	65	64	SMD.5	FT0079
SFC35N12OJ	1200	30	80	96	46	65	86	T0-257	FT0079
SFC57N170S1	1700	57	45	70	188	Note 1	227	SMD1	FT0082
SFC57N170S1L	1700	57	45	70	188	Note 1	227	SMD1 with leads	FT0082

1/ Contact factory for more information

### For high reliability aerospace and defense applications such as:

- High voltage DC-DC converters
- Switch mode power supplies
- Solar inverters
- Motor drive
- Pulsed power applications









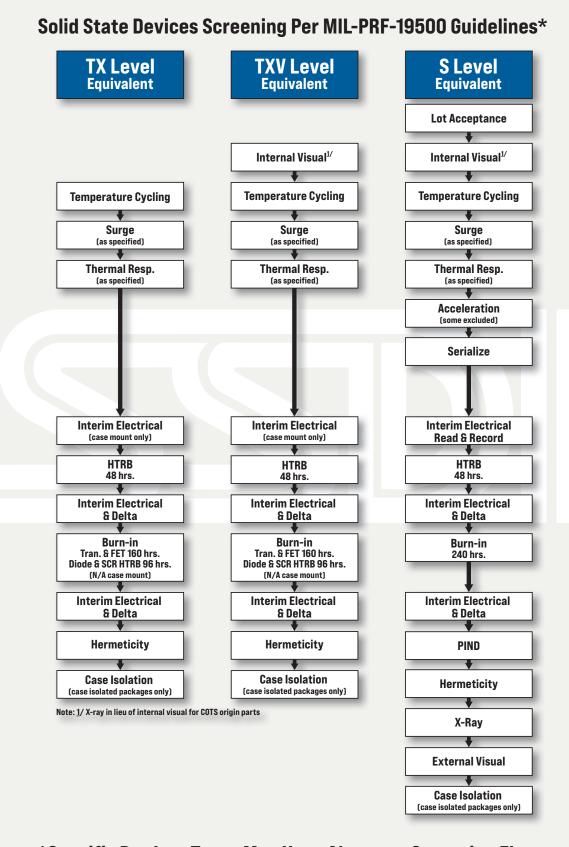




Contact SSDI to request samples or discuss specific program requirements:

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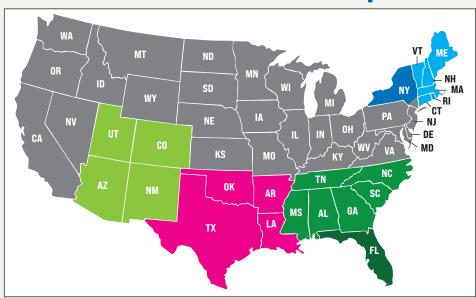




## \*Specific Product Types May Have Alternate Screening Flows

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